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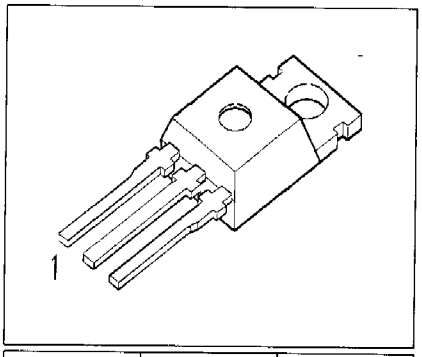
BUZ 72A

- N channel
- Enhancement mode
- Avalanche-rated



Pin 1	Pin 2	Pin 3
G	D	S

Type	V_{DS}	I_D	$R_{DS(on)}$	Package
BUZ 72 A	100 V	9 A	0.25 Ω	TO-220 AB

Maximum Ratings

Parameter	Symbol	Values	Unit
Continuous drain current T_C = 25 °C	I_D	9	A
Pulsed drain current T_C = 25 °C	I_{Dpuls}	36	
Avalanche current,limited by T_{jmax}	I_{AR}	10	
Avalanche energy,periodic limited by T_{jmax}	E_{AR}	7.9	mJ
Avalanche energy, single pulse I_D = 10 A, V_{DD} = 25 V, R_{GS} = 25 Ω L = 885 µH, T_j = 25 °C	E_{AS}	59	
Gate source voltage	V_{GS}	± 20	V
Power dissipation T_C = 25 °C	P_{tot}	40	W
Operating temperature	T_j	-55 ... + 150	°C
Storage temperature	T_{stg}	-55 ... + 150	
Thermal resistance, chip case	R_{thJC}	≤ 3.1	K/W
Thermal resistance, chip to ambient	R_{thJA}	75	
DIN humidity category, DIN 40 040		E	
IEC climatic category, DIN IEC 68-1		55 / 150 / 56	

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

Electrical Characteristics, at T_j = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain- source breakdown voltage V_{GS} = 0 V, I_D = 0.25 mA, T_j = 25 °C	$V_{(BR)DSS}$	100	-	-	V
Gate threshold voltage V_{GS}=V_{DS}, I_D = 1 mA	$V_{GS(th)}$	2.1	3	4	
Zero gate voltage drain current V_{DS} = 100 V, V_{GS} = 0 V, T_j = 25 °C V_{DS} = 100 V, V_{GS} = 0 V, T_j = 125 °C	I_{DSS}	- -	0.1 10	1 100	µA
Gate-source leakage current V_{GS} = 20 V, V_{DS} = 0 V	I_{GSS}	-	10	100	nA
Drain-Source on-resistance V_{GS} = 10 V, I_D = 6 A	$R_{DS(on)}$	-	0.2	0.25	Ω

Electrical Characteristics, at T_j = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Transconductance $V_{DS} \geq 2 * I_D * R_{DS(on)max}$, I_D = 6 A	g_{fs}	3	4.3	-	S
Input capacitance V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz	C_{iss}	-	400	530	pF
Output capacitance V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz	C_{oss}	-	120	180	
Reverse transfer capacitance V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz	C_{rss}	-	70	105	
Turn-on delay time V_{DD} = 30 V, V_{GS} = 10 V, I_D = 3 A R_{GS} = 50 Ω	$t_{d(on)}$	-	10	15	ns
Rise time V_{DD} = 30 V, V_{GS} = 10 V, I_D = 3 A R_{GS} = 50 Ω	t_r	-	45	70	
Turn-off delay time V_{DD} = 30 V, V_{GS} = 10 V, I_D = 3 A R_{GS} = 50 Ω	$t_{d(off)}$	-	55	75	
Fall time V_{DD} = 30 V, V_{GS} = 10 V, I_D = 3 A R_{GS} = 50 Ω	t_f	-	40	55	

Electrical Characteristics, at T_j = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Reverse Diode					
Inverse diode continuous forward current T_C = 25 °C	I_S	-	-	9	A
Inverse diode direct current,pulsed T_C = 25 °C	I_{SM}	-	-	36	
Inverse diode forward voltage V_{GS} = 0 V, I_F = 20 A	V_{SD}	-	1.4	1.6	V
Reverse recovery time V_R = 30 V, I_F=I_S, di_F/dt = 100 A/µs	t_{rr}	-	170	-	ns
Reverse recovery charge V_R = 30 V, I_F=I_S, di_F/dt = 100 A/µs	Q_{rr}	-	0.3	-	µC